e5130

Low Voltage CMOS Driver Circuit

Description

The e5130 contains 4 independent driver outputs with an ON resistance of typ. 25 Ω (15 Ω) tor the P-channel output transistors and typ. 20 Ω (13 Ω) for the N-channel output transistors; at a supply voltage of 1.5 V (3 V). To obtain a fast transition of the outputs, even for slow rise/-fall time input signals, all digital inputs (IN1 ... IN4) have a schmitt-trigger characteristic; with a hysteresis of

typ. 50 mV. If a higher driving capability is needed, all inputs and outputs may be connected in parallel. In this case the rise/-fall time of the input signals IN1 ... IN4 must be less than 200 nsec. Due to the fast switching characteristic of the tristatable output drivers, the circuit is also suited as low voltage bus driver.

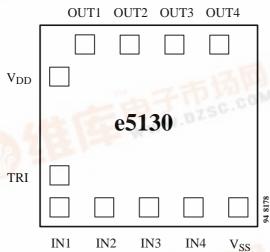
Features

- 1.1 3.6 V operating voltage range
- 4 non-inverting, tristatable drivers for the following applications:
- Motor driver for bipolar stepper motors in watch/clock applications
- Driver for piezoelectric transducers (buzzer)
- LED Driver
- Line driver for medium speed applications

Advantages

- High load current at low supply voltage
- Replaces several discrete transistors
- Tri-state operation possible
- Possible applications:
- Motor driver
- Radio controlled clock/watch
- Line driver for mini-computer, laptop
- LED driver
- Relay driver

Pad Configuration



Name	Description			
V _{DD}	Positive supply voltage			
V _{SS}	Negative supply voltage			
IN1 IN4	Digital inputs			
TRI	Tristate input			
OUT1 OUT4	Drive outputs			

Chipsize: x = 1.08 mm, y = 1.42 mm,
Padwindow: 90 x 90 µ

Ordering Information

Extended Type Number	Package	Remarks	
e5130A–DIT	Die	Die in Trays	





Absolute Maximum Ratings

Absolute maximum ratings define parameter limits which, it exceeded, may permanently change or damage the device. All inputs and outputs on circuits are highly protected against electrostatic discharges.

However, precautions to minimize build-up of electrostatic charges during handling are recommended.

The circuits are protected against supply voltage reversal for typically 5 minutes, if the current is limited to 120 mA.

Parameters	Symbol	Value	Unit
Supply voltage	$V_{DD} - V_{SS}$	-0.3 to + 5	V
Input voltage range, all inputs	$V_{\rm I}$	$V_{SS} - 0.3$ to $V_{DD} + 0.3$	V
Operating ambient temperature range		-20 to + 70	°C
Storage temperature range		- 40 to + 125	°C
Lead temperature during soldering at 2 mm distance, 10 s		260	°C

Operating Characteristics

 $V_{SS}=0$ V, $V_{DD}=+$ 1.5 V, $T_{amb}=+$ 25 °C, unless otherwise specified. All voltage levels are measured with reference to V_{SS} .

Parameters	Test Conditions / Pin	Symbol	Min	Тур	Max	Unit		
Operating voltage		V_{DD}	1.1		3.6	V		
Operating temperature		T _{amb}	- 10		60	°C		
Operating current (standby)	$V_{DD} = 3.6 \text{ V}, R_{L12} = R_{L34} = \infty,$ IN1 to IN4 at V_{DD} or V_{SS} , TRI at V_{SS}	I _{DD}		0.05	1	μΑ		
Drive output OUT1 to OUT4	Drive output OUT1 to OUT4							
Output current	$V_{DD} = 1.2 \text{ V}, R_{L12} = R_{L34} = 200 \Omega$	I _{OUT}	± 4.3	± 4.75		mA		
Output current	$V_{DD} = 1.5 \text{ V}, R_{L12} = R_{L34} = 200 \Omega$	I _{OUT}	± 5.7	± 6.20		mA		
Output current	$V_{DD} = 3.0 \text{ V}, R_{L12} = R_{L34} = 200 \Omega$	I _{OUT}	± 12	± 13		mA		
Delay time	$V_{DD} = 3 \text{ V}, C_L = 50 \text{ pF}$	T _{Dr} , T _{Df}		35	60	ns		
Delay time	$V_{DD} = 1.5 \text{ V}, C_L = 50 \text{ pF},$ see figure 2, note 1	T _{Dr} , T _{Df}		80	150	ns		
Rise/-fall time	$V_{DD} = 3 \text{ V}, C_L = 50 \text{ pF}$	t _r , t _f		8	15	ns		
Rise/-fall time	$V_{DD} = 1.5 \text{ V}, C_L = 50 \text{ pF},$ see figure 2, note 2	t_r, t_f		12	25	ns		
Digital input IN1 to IN4								
Input current	$V_{IL} = 0 V$	I_{IL}			-100	nA		
Input current	$V_{IH} = V_{DD}$	I _{IH}			100	nA		
Threshold	V	V_{TH}		$V_{DD}/2$		V		
Hysteresis	mV	V _{HYST}		50		mV		
Tristate input TRI								
Input current TRI	$V_{IH} = V_{DD}$	I_{IH}	0.15	0.4	1.2	μΑ		

2 (4) Rev. A2, 13-Mar-01



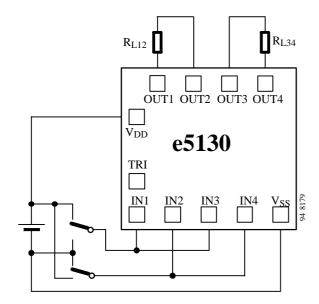
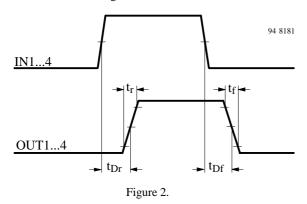


Figure 1. Test circuit



Note 1: t_{Dr} , t_{Df} is defined at 50% of supply voltage Note 2: t_r , t_f is defined from 10% to 90%, resp. 90% to 10% of supply voltage

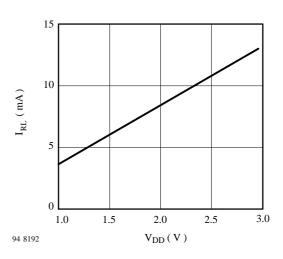


Figure 3. Typical current into 200 Ω load resistor, condition as $$\operatorname{\textsc{per}}$$ figure 1

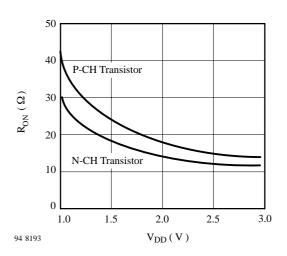


Figure 4. Typical output on-resistance vs. supply voltage at $V_{DS} = 0.2 \; V \label{eq:VDS}$

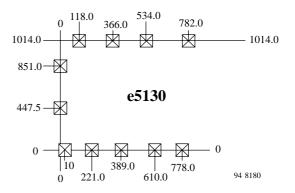
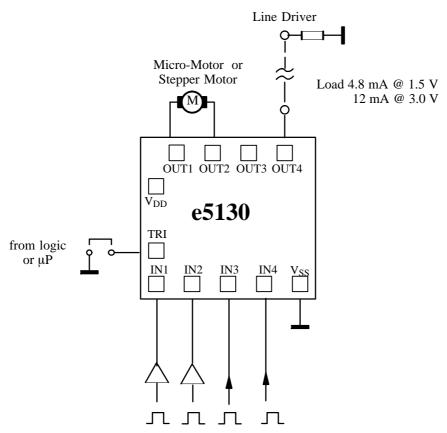


Figure 5. Pad coordinates

Rev. A2, 13-Mar-01 3 (4)



Application Circuit



We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Atmel Wireless & Microcontrollers products for any unintended or unauthorized application, the buyer shall indemnify Atmel Wireless & Microcontrollers against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Data sheets can also be retrieved from the Internet: http://www.atmel-wm.com

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4 (4) Rev. A2, 13-Mar-01